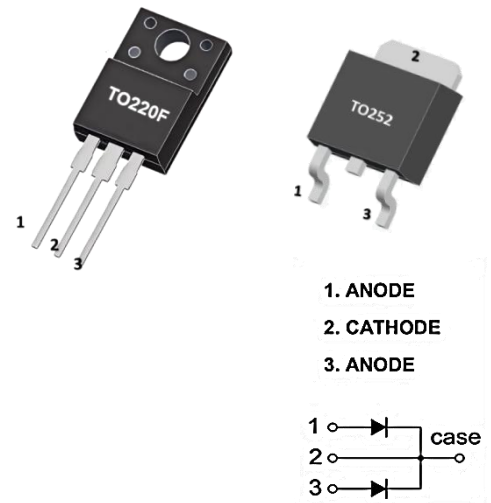


DESCRIPTION

The MBR(D/F)20100CS meet the ROHS and Green Product requirement with full function reliability approved.

FEATURE

- * Schottky Barrier Chip
- * Guard Ring Die Construction for Transient Protection
- * Low Power Loss,High Efficiency
- * High Surge Capability
- * High Current Capability and Low Forward Voltage Drop
- * For Use in Low Voltage, High Frequency Inverters,Free Wheeling, and Polarity Protection Applications



ABSOLUTE MAXIMUM RATINGS(TA=25°C, unless otherwise specified.)

SYMBOL	PARAMETER		VALUE	UNIT
VRRM	Peak repetitive reverse voltage		100	V
VRWM	Working peak reverse voltage		100	V
VR	DC blocking voltage		100	V
VR(RMS)	RMS reverse voltage		70	V
IO	Average rectified output current		20 (10*2)	A
IFSM	Non-Repetitive peak forward surge current(8.3ms half sine wave)		150*2	A
Tj	Junction temperature		175	°C
Tstg	Storage temperature		-55 ~ +150	°C
Cj (Ctot)	Typical total capacitance(VR=5V,f=1MHz)		500	pF
RθJA	Thermal Resistance from Junction to Ambient	TO-252	100	°C/W
		TO-220F	58	
RθJC	Thermal Resistance From Junction To Case	TO-252	5	°C/W
		TO-220F	3	

Notes: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (TA=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN	TYP	MAX	UNIT
Reverse voltage	V(BR)	I R=0.2mA		100			V
Reverse current	I R	VR=100V	Tj =25°C			5	uA
			Tj =125°C		5.0		mA
Forward voltage	VF	I F=5A	Tj =25°C			0.8	V
			Tj =125°C		0.60		V
		I F=10A	Tj =25°C			0.95	V
			Tj =125°C		0.68		V

*Pulse test: pulse width ≤300μs, duty cycle≤ 2.0%

■ TYPICAL CHARACTERISTICS

